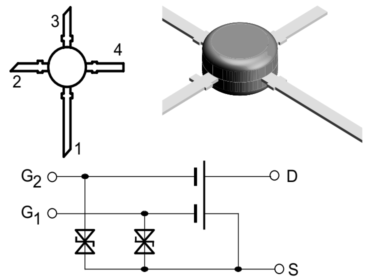
N-Channel Dual Gate MOS-Fieldeffect Tetrode, Depletion Mode

Features

- Integrated gate protection diodes
- High cross modulation performance
- Low noise figure
- High AGC-range
- Low feedback capacitance
- Low input capacitance
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Electrostatic sensitive device.
Observe precautions for handling.

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Applications

Input- and mixer stages especially UHF-tuners.

Mechanical Data

Case: TO-50 Plastic case
Weight: approx. 124 mg
Marking: BF966S
Pinning:
1 = Drain, 2 = Source,
3 = Gate 1, 4 = Gate 2

Parts Table

Part	Ordering Ccode	Marking	Package
BF966S	BF966SA or BF966SB	BF966S	TO50
BF966SA	BF966SA	BF966S	TO50
BF966SB	BF966SB	BF966S	TO50

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Drain - source voltage		V_{DS}	20	V
Drain current		I_D	30	mA
Gate 1/Gate 2 - source peak current		$\pm I_{G1/G2SM}$	10	mA
Total power dissipation	$T_{amb} \le 60$ °C	P_{tot}	200	mW
Channel temperature		T_{Ch}	150	°C
Storage temperature range		T_{stg}	- 55 to + 150	°C

Maximum Thermal Resistance

Parameter	Test condition	Symbol	Value	Unit
Channel ambient	1)	R_{thChA}	450	K/W

1) on glass fibre printed board (40 x 25 x 1.5) mm^3 plated with 35 µm Cu

Electrical DC Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Drain - source breakdown voltage	I_D = 10 µA, - V_{G1S} = - V_{G2S} = 4 V		$V_{(BR)DS}$	20			V
Gate 1 - source breakdown voltage	± I_{G1S} = 10 mA, V_{G2S} = V_{DS} = 0		± $V_{(BR)G1SS}$	8		14	V
Gate 2 - source breakdown voltage	± I_{G2S} = 10 mA, V_{G1S} = V_{DS} = 0		± $V_{(BR)G2SS}$	8		14	V
Gate 1 - source leakage current	± V_{G1S} = 5 V, V_{G2S} = V_{DS} = 0		± I_{G1SS}			50	nA
Gate 2 - source leakage current	± V_{G2S} = 5 V, V_{G1S} = V_{DS} = 0		± I_{G2SS}			50	nA
Drain current	V_{DS} = 15 V, V_{G1S} = 0, V_{G2S} = 4 V	BF966S	I_{DSS}	4		18	mA
		BF966SA	I_{DSS}	4		10.5	mA
		BF966SB	I_{DSS}	9.5		18	mA
Gate 1 - source cut-off voltage	V_{DS} = 15 V, V_{G2S} = 4 V, I_D = 20 µA		-$V_{G1S(OFF)}$			2.5	V
Gate 2 - source cut-off voltage	V_{DS} = 15 V, V_{G1S} = 0, I_D = 20 µA		-$V_{G2S(OFF)}$			2.0	V

Electrical AC Characteristics

T_{amb} = 25 °C, unless otherwise specified
V_{DS} = 15 V, I_D = 10 mA, V_{G2S} = 4 V, f = 1 MHz

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward transadmittance		$\| y_{21s} \|$	15	18.5		mS
Gate 1 input capacitance		C_{issg1}		2.2	2.6	pF
Gate 2 input capacitance	V_{G1S} = 0, V_{G2S} = 4 V	C_{issg2}		1.1		pF
Feedback capacitance		C_{rss}		25	35	fF
Output capacitance		C_{oss}		0.8	1.2	pF
Power gain	G_S = 2 mS, G_L = 0.5 mS, f = 200 MHz	G_{ps}		25		dB
	G_S = 3,3 mS, G_L = 1 mS, f = 800 MHz	G_{ps}		18		dB
AGC range	V_{G2S} = 4 to -2 V, f = 800 MHz	ΔG_{ps}	40			dB
Noise figure	G_S = 2 mS, G_L = 0.5 mS, f = 200 MHz	F		1.0		dB
	G_S = 3,3 mS, G_L = 1 mS, f = 800 MHz	F		1.8		dB

Typical Characteristics (Tamb = 25 °C unless otherwise specified)

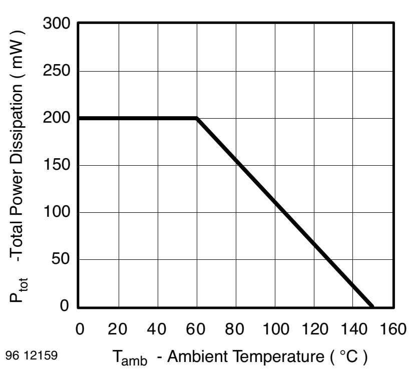


Figure 1. Total Power Dissipation vs. Ambient Temperature

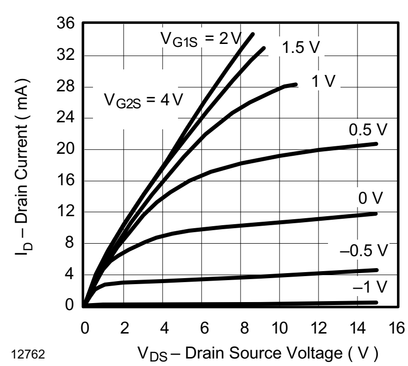


Figure 2. Drain Current vs. Drain Source Voltage

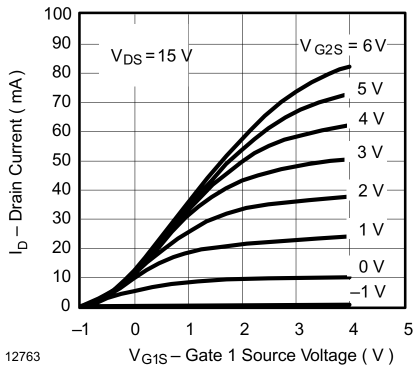


Figure 3. Drain Current vs. Gate 1 Source Voltage

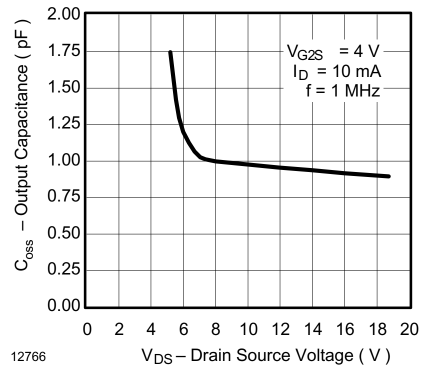


Figure 6. Output Capacitance vs. Drain Source Voltage

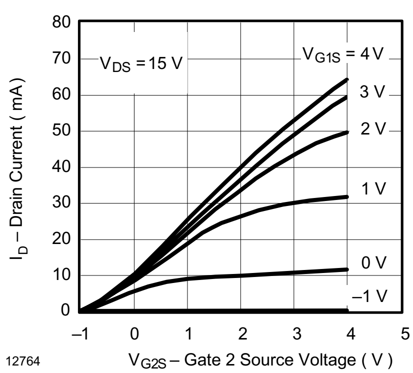


Figure 4. Drain Current vs. Gate 2 Source Voltage

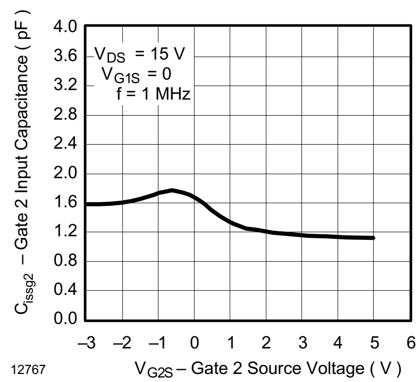


Figure 7. Gate 2 Input Capacitance vs. Gate 2 Source Voltage

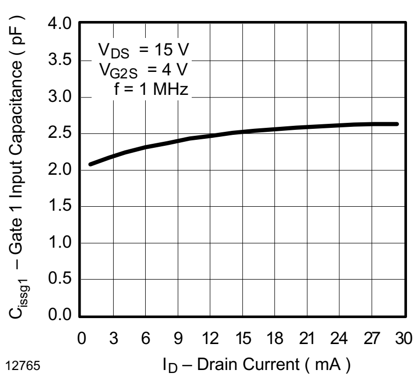


Figure 5. Gate 1 Input Capacitance vs. Drain Current

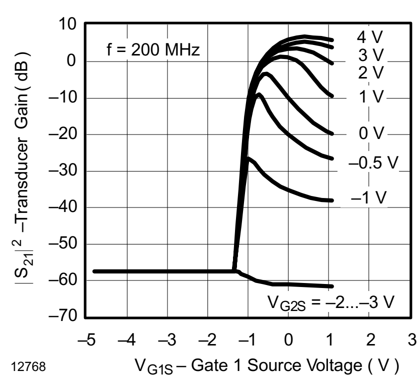


Figure 8. Transducer Gain vs. Gate 1 Source Voltage

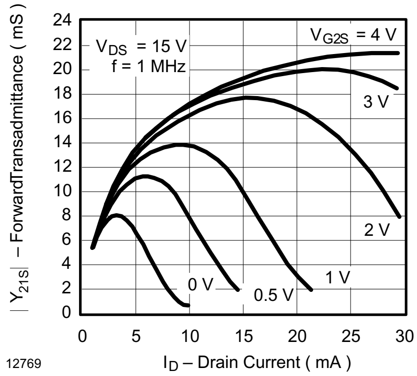


Figure 9. Forward Transadmittance vs. Drain Current

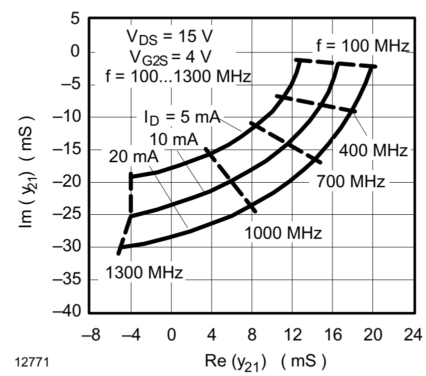


Figure 12. Short Circuit Forward Transfer Admittance

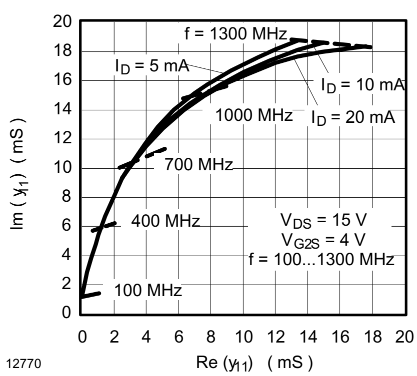


Figure 10. Short Circuit Input Admittance

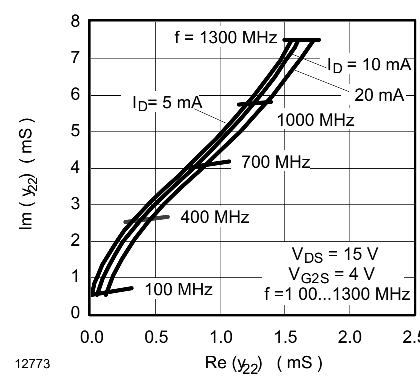


Figure 13. Short Circuit Output Admittance

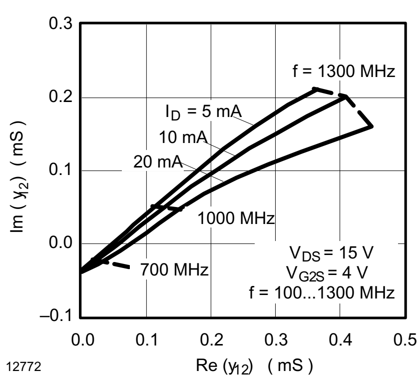


Figure 11. Short Circuit Reverse Transfer Admittance

V_{DS} = 15 V, I_D = 5 to 20 mA, V_{G2S} = 4 V, Z_0 = 50 Ω

S_{11}

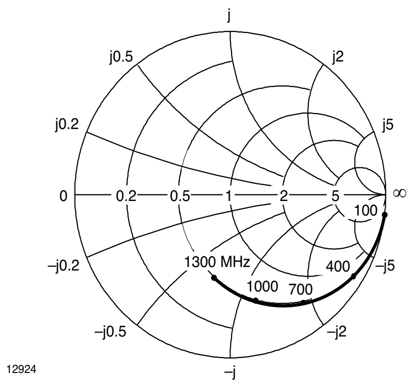


Figure 14. Input Reflection Coefficient

S_{12}

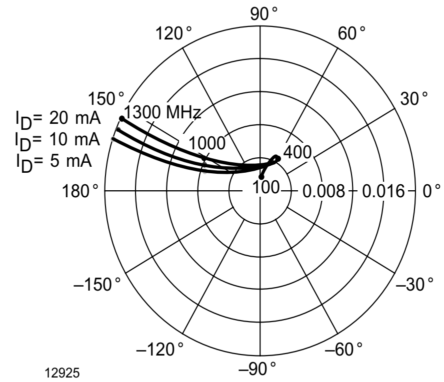


Figure 16. Reverse Transmission Coefficient

S_{21}

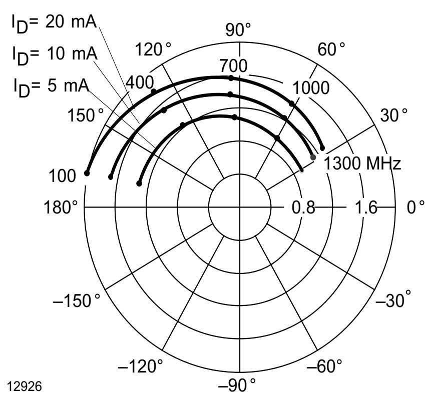


Figure 15. Forward Transmission Coefficient

S_{22}

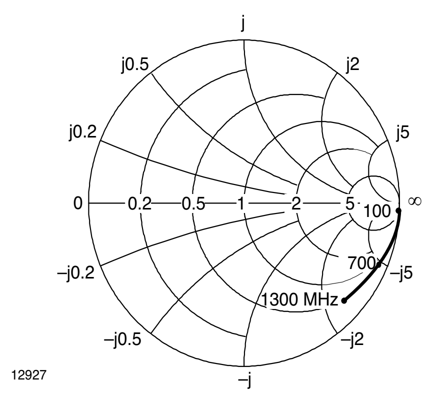
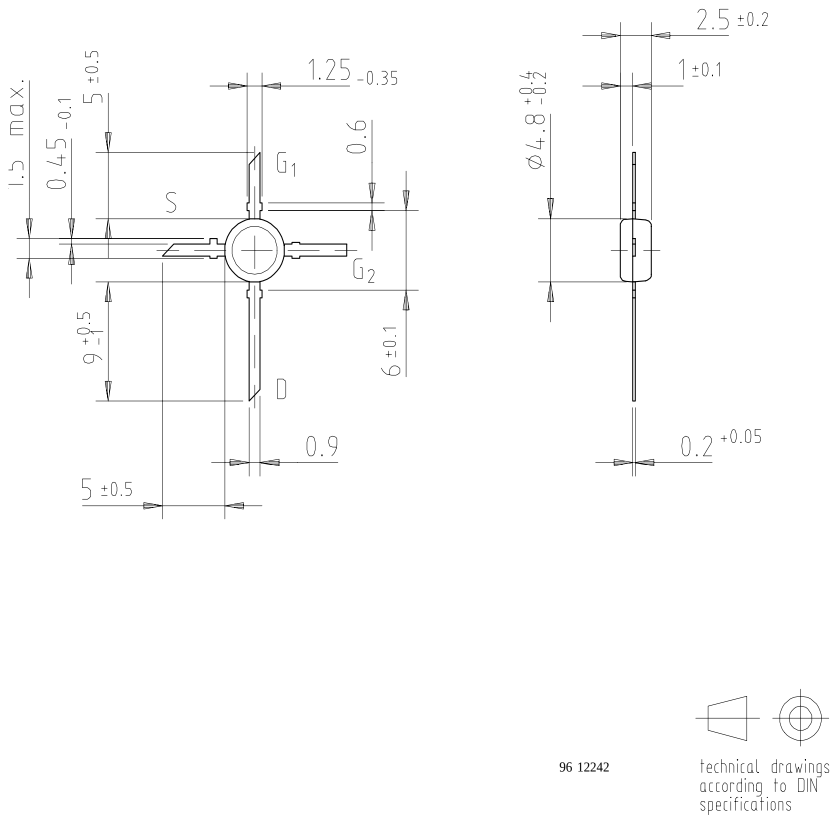


Figure 17. Output Reflection Coefficient

Package Dimensions in mm



Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

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